

HVM131SR

Silicon Epitaxial Planar Pin Diode for Antenna Switching

HITACHI

Rev. 1
Oct. 1995

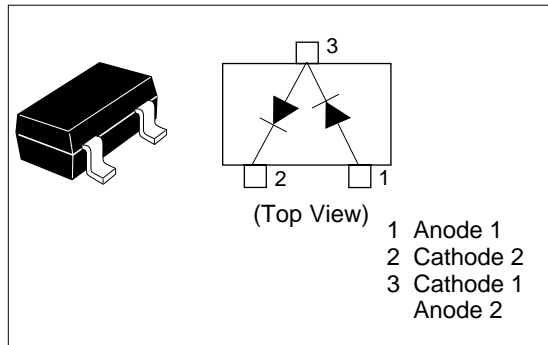
Features

- Low capacitance. (C=0.8pF max)
- Low forward resistance. ($r_f=1.0\Omega$ max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HVM131SR	P6	MPAK

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	65	V
Reverse voltage	V_R	60	V
Forward current	I_F^*	100	mA
Power dissipation	P_d^*	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

* Two device total

Electrical Characteristics ($T_a = 25^\circ\text{C}$) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 10 \text{ mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 60 \text{ V}$
Capacitance	C	—	—	0.8	pF	$V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$
Forward resistance	r_f	—	—	1.0	Ω	$I_F = 10 \text{ mA}$, $f = 100 \text{ MHz}$

* Per one device

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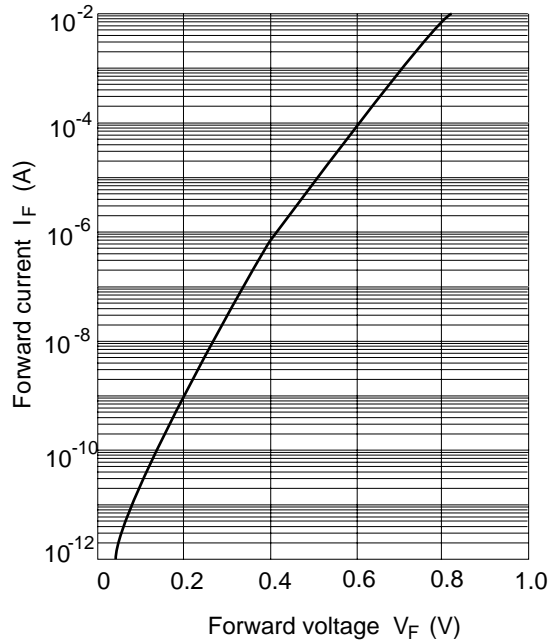


Fig.1 Forward current Vs. Forward voltage

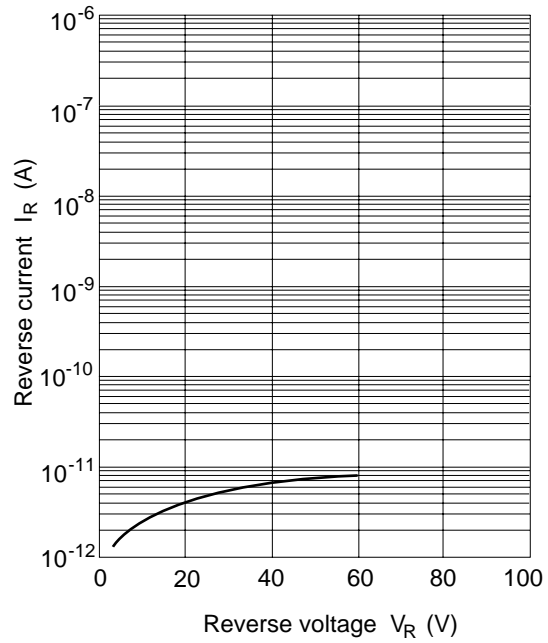


Fig.2 Reverse current Vs. Reverse voltage

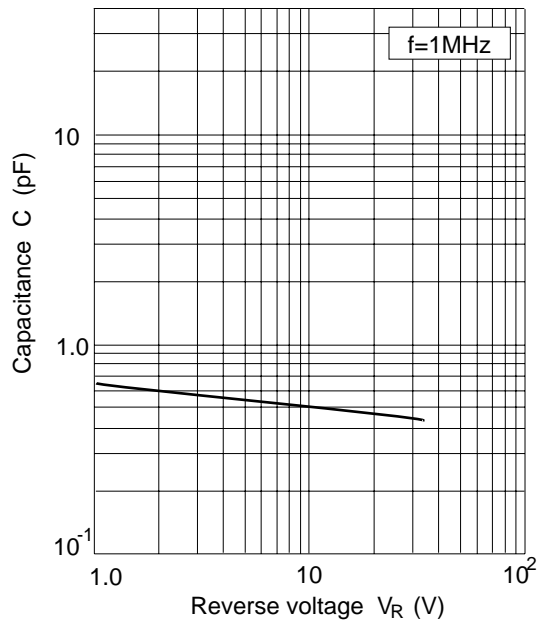


Fig.3 Capacitance Vs. Reverse voltage

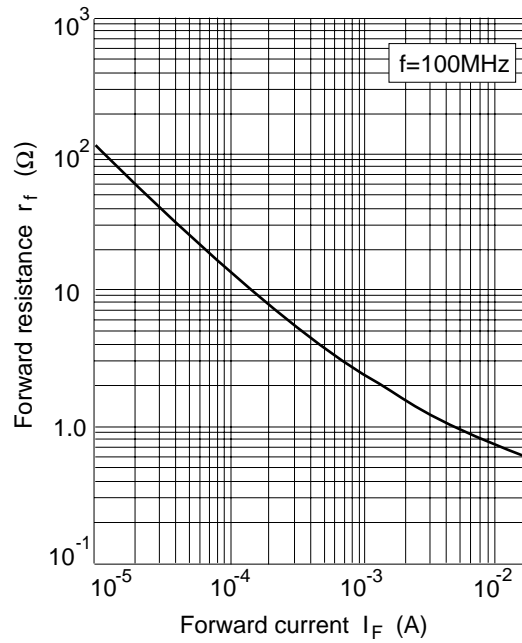


Fig.4 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm

